

ABSTRACT OF THE DISCLOSURE

The invention includes methods of forming material on a substrate and methods of forming a field effect transistor gate oxide. In one implementation, a first species monolayer is chemisorbed onto a substrate

within a chamber from a gaseous first precursor. The first species monolayer is discontinuously formed over the substrate. The substrate having the

discontinuous first species monolayer is exposed to a gaseous second precursor different from the first precursor effective to react with the first species to form a second species monolayer, and effective to form a reaction

product of the second precursor with substrate material not covered by the first species monolayer. The substrate having the second species monolayer

and the reaction product is exposed to a third gaseous substance different from the first and second precursors effective to selectively remove the reaction product from the substrate relative to the second species monolayer.

Other implementations are contemplated.